



80V N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI[®]

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
80V	$17m\Omega @ V_{GS} = 10V$	65A
60 V	$21m\Omega$ @ $V_{GS} = 4.5V$	59A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

POWERDI®5060-8

- Synchronous Rectifier
- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

Features

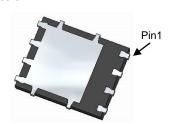
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

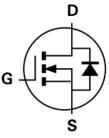
- Case: POWERDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208@3
- Weight: 0.097 grams (Approximate)



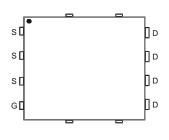




Bottom View



Internal Schematic



Top View Pin Configuration

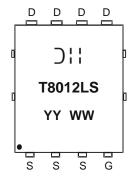
Ordering Information (Note 4)

I		
Part Number	Case	Packaging
DMT8012LPS-13	POWERDI®5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- <1000ppm antimony compounds.</p>
 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



] | = Manufacturer's Marking T8012LS = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 14 = 2014) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	I _D	9 7.2	А
Continuous Drain Current, V _{GS} = 10V (Note 6)	$T_C = +25$ °C $T_C = +70$ °C	I _D	65 51	А
Maximum Continuous Body Diode Forward Current (Note 6)		Is	80	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	80	Α
Avalanche Current, L=0.1mH		I _{AS}	11.6	Α
Avalanche Energy, L=0.1mH		E _{AS}	10.2	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	56	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	P_D	113	W
Thermal Resistance, Junction to Case (Note 6)		R ₀ JC	1.1	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	80	-	-	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 64V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	=	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	1	1.3	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	-	14	17	mΩ	$V_{GS} = 10V, I_D = 12A$	
Static Dialif-Source Off-Nesistance	R _{DS(ON)}	-	16.5	21		$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V_{SD}	=	0.9	1.2	٧	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	1,949	-		$V_{DS} = 40V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	-	177	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	10	-			
Gate Resistance	R_g	-	0.7	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	=	15	-			
Total Gate Charge (V _{GS} = 10V)	Qg	=	34	1	nC	$V_{DS} = 40V, I_D = 12A$	
Gate-Source Charge	Q_{gs}	-	6	-	110		
Gate-Drain Charge	Q_{gd}	-	4.5	-			
Turn-On Delay Time	t _{D(ON)}	-	4.9	-		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 12A, R_{G} = 1.6\Omega$	
Turn-On Rise Time	t _R	=	3.8	-			
Turn-Off Delay Time	t _{D(OFF)}	=	16.5	-	ns		
Turn-Off Fall Time	t _F	=	3.5	-			
Body Diode Reverse Recovery Time	t _{RR}	=	30.2	-	ns	I_ 12A di/dt 100A/vo	
Body Diode Reverse Recovery Charge	Qrr	-	34.6	-	nC	I _F = 12A, di/dt = 100A/μs	

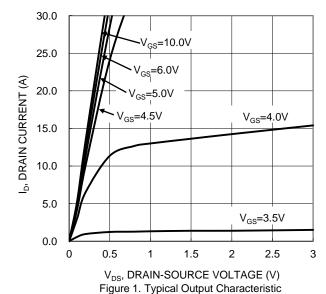
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

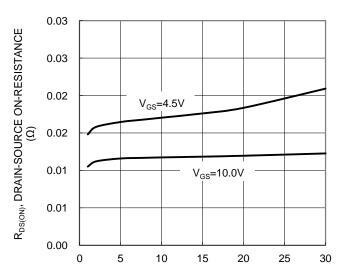
^{6.} Thermal resistance from junction to soldering point (on the exposed drain pad).

^{7.} Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

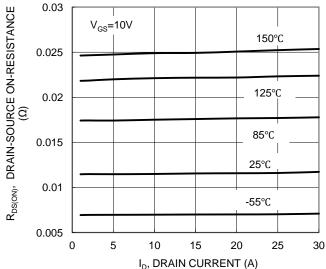


Figure 5. Typical On-Resistance vs Drain Current and Temperature

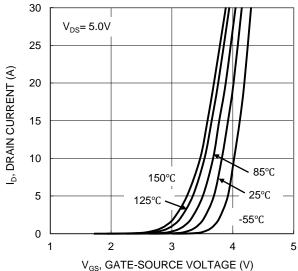
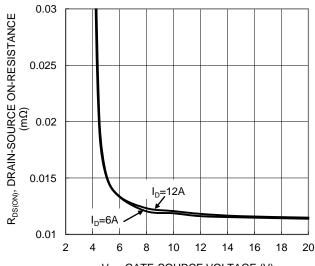


Figure 2. Typical Transfer Characteristic



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

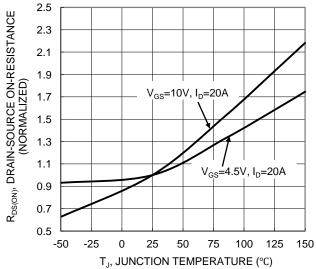


Figure 6. On-Resistance Variation with Temperature



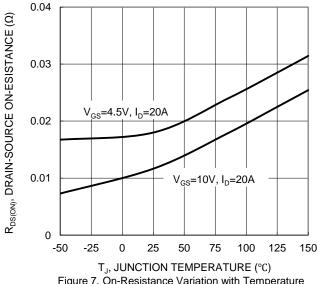


Figure 7. On-Resistance Variation with Temperature

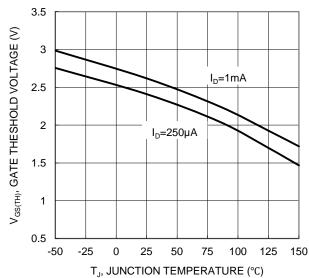


Figure 8. Gate Theshold Variation vs Temperature

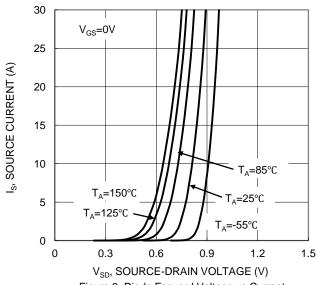
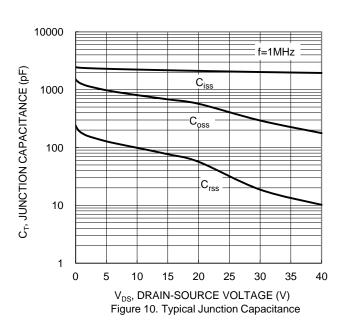
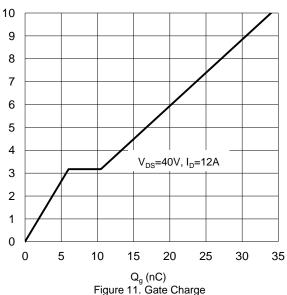
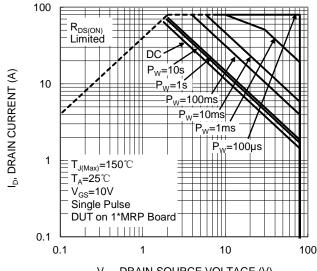


Figure 9. Diode Forward Voltage vs Current







V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



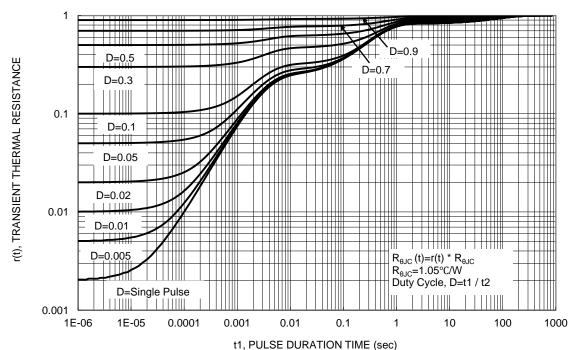
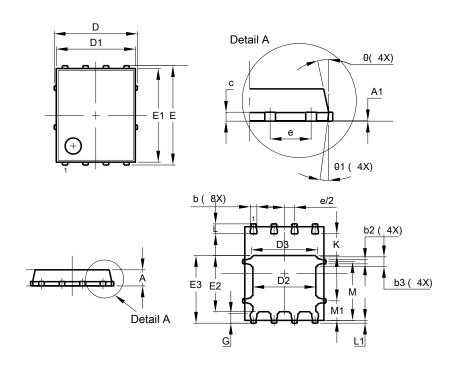


Figure 13. Transient Thermal Resistance



Package Outline

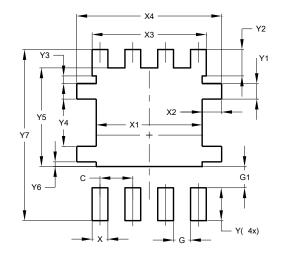
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



POWERDI®5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
C	0.230	0.330	0.277		
D	5.15 BSC				
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(3.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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